

## NCE N-Channel Super Trench Power MOSFET

### Description

The NCEP40T14G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

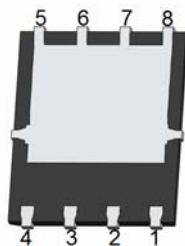
- $V_{DS} = 40V, I_D = 140A$   
 $R_{DS(ON)} = 1.6m\Omega$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 2.3m\Omega$  (typical) @  $V_{GS} = 4.5V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100%  $\Delta V_{ds}$  TESTED!**

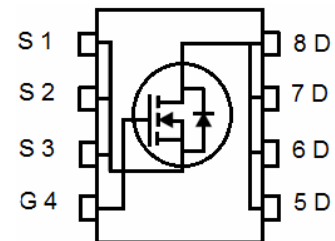
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T14G	NCEP40T14G	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous (Silicon Limited)	$I_D$	140	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	99	A
Pulsed Drain Current (Package Limited)	$I_{DM}$	400	A
Maximum Power Dissipation	$P_D$	133	W
Derating factor		1.06	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	980	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	0.94	$^\circ C/W$
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## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	1.6	1.9	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	2.3	2.65	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		75	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	5000	-	PF
Output Capacitance	C <sub>oss</sub>		-	1950	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	110	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	12	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	6.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	49	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	90	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	17	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	14	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	140	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	24	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs (Note 3)	-	85	-	nC

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=20V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

Typical Electrical and Thermal Characteristics

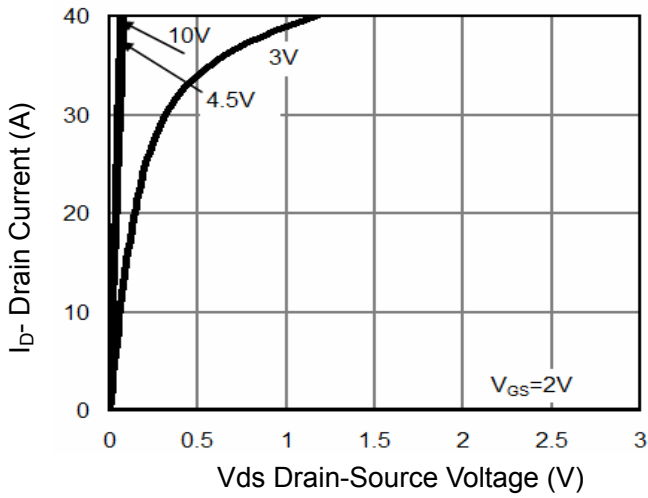


Figure 1 Output Characteristics

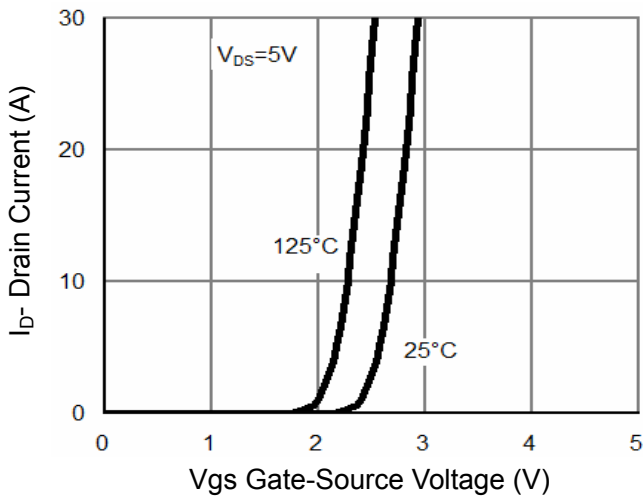


Figure 2 Transfer Characteristics

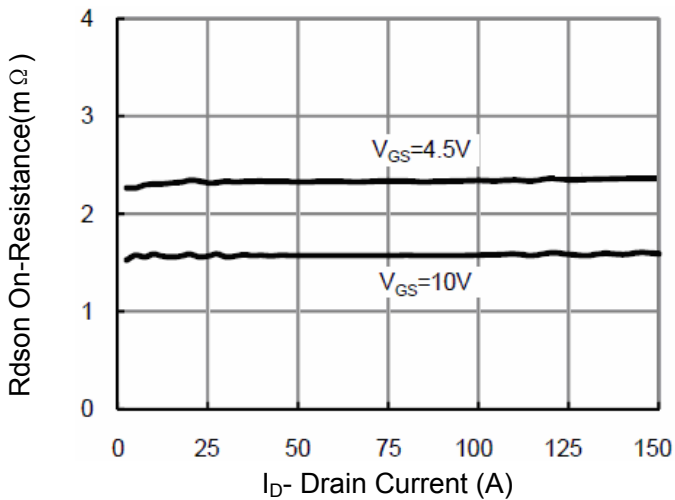


Figure 3 Rdson- Drain Current

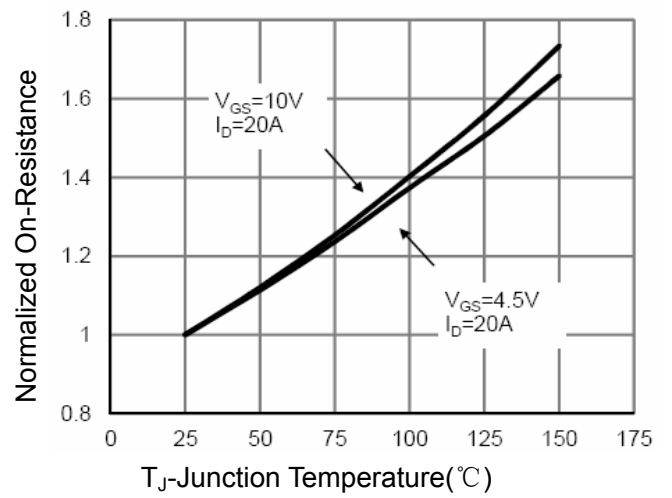


Figure 4 Rdson-Junction Temperature

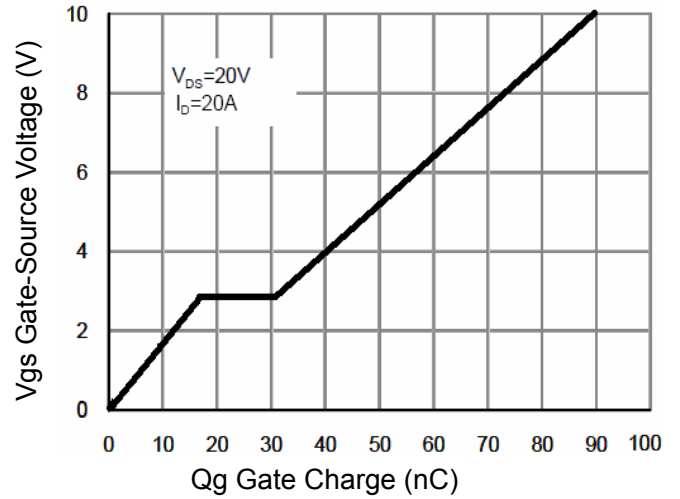


Figure 5 Gate Charge

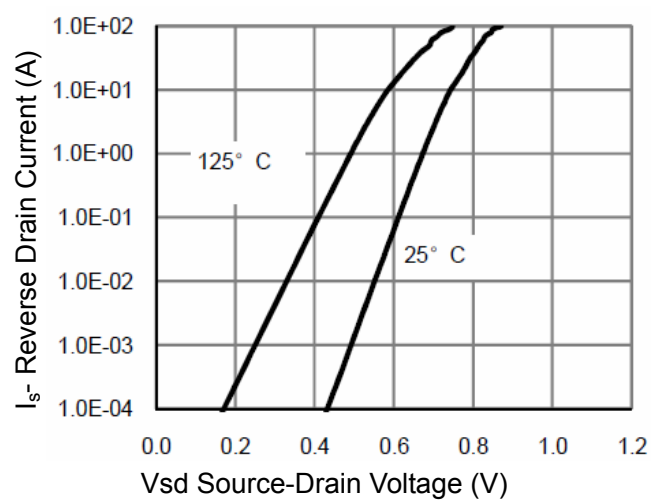


Figure 6 Source- Drain Diode Forward

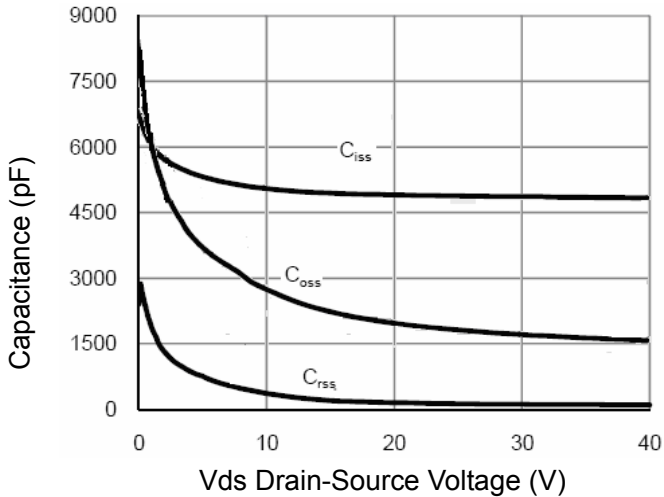


Figure 7 Capacitance vs Vds

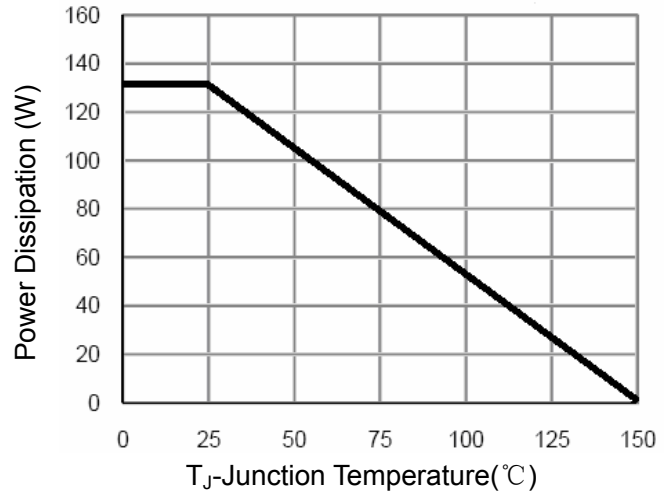


Figure 9 Power De-rating

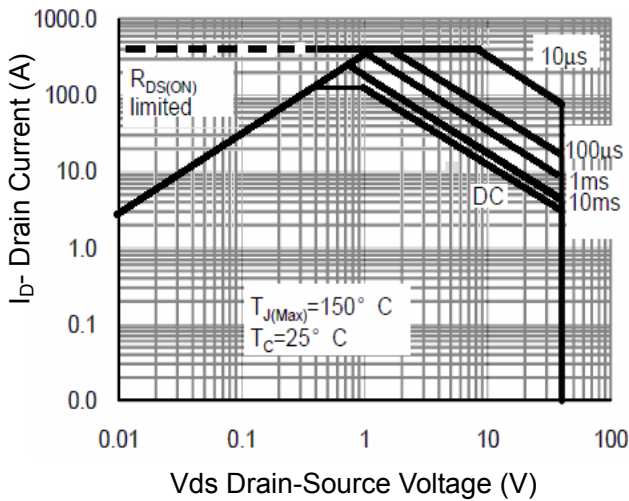


Figure 8 Safe Operation Area

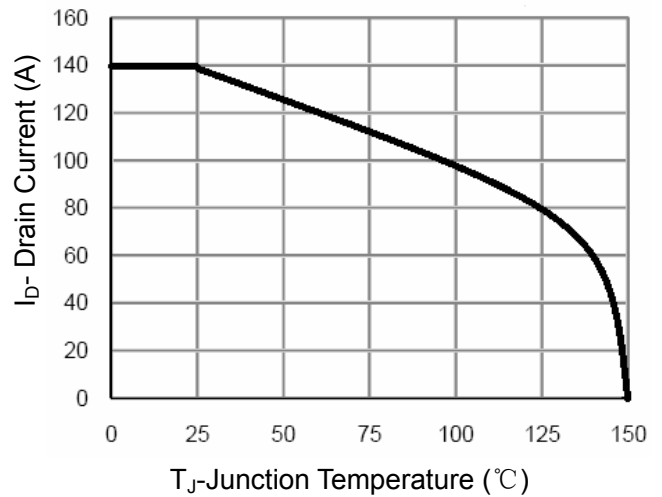


Figure 10 Current De-rating

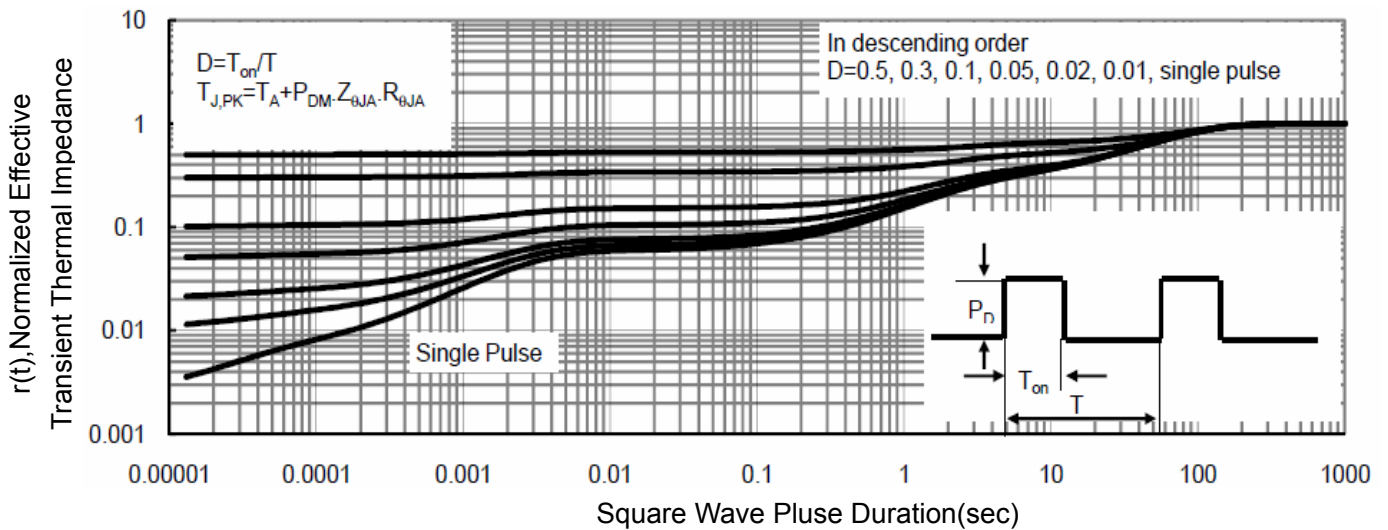
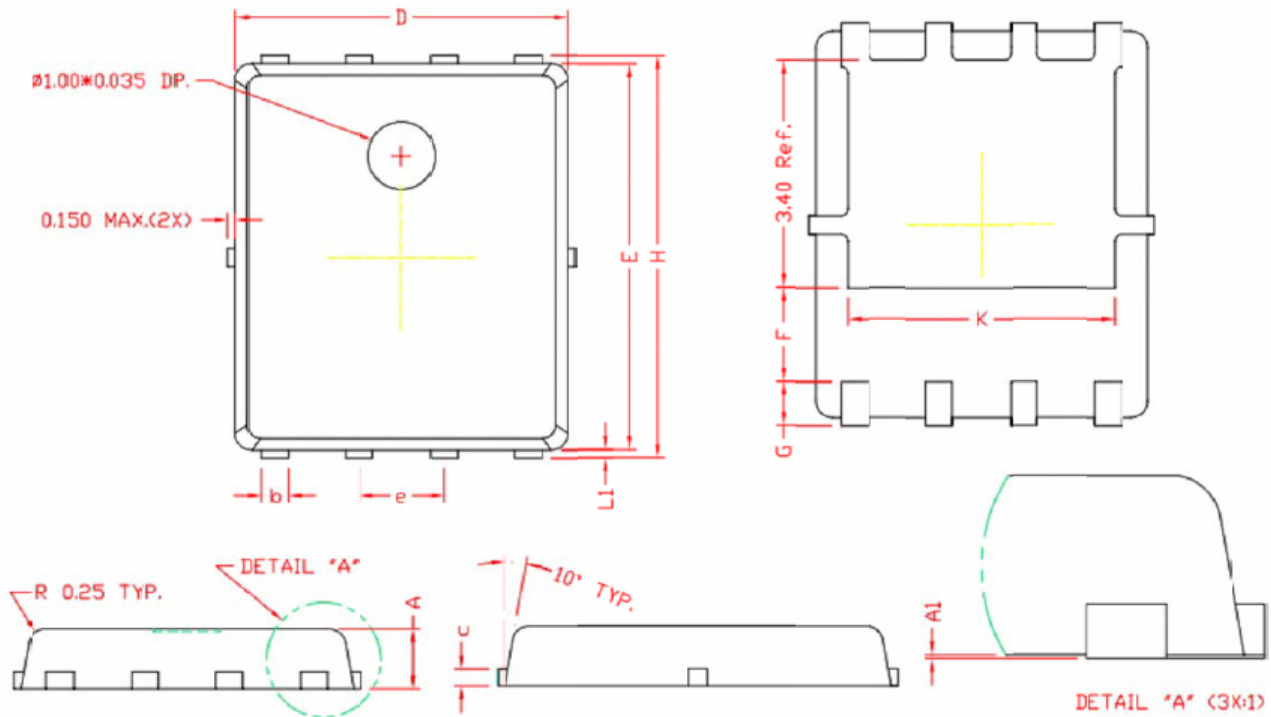


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
b	0.35	0.42	0.49
c	0.254 REF.		
D	4.90	5.00	5.10
F	1.40 REF.		
E	5.70	5.80	5.90
e	1.27 BSC.		
H	5.95	6.08	6.20
L1	0.10	0.14	0.18
G	0.60 REF.		
K	4.00 REF.		

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